



STD85N3LH5 STP85N3LH5 - STU85N3LH5

N-channel 30 V, 0.0042 Ω , 80 A, DPAK, TO-220, IPAK
STripFET™ V Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STD85N3LH5	30 V	< 0.005 Ω	80 A
STP85N3LH5	30 V	< 0.0054 Ω	80 A
STU85N3LH5	30 V	< 0.0054 Ω	80 A

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness
- Low gate drive power losses

Application

- Switching applications

Description

This product utilizes the 5th generation of design rules of ST's proprietary STripFET™ technology. The lowest available R_{DS(on)} * Q_g, in the standard packages, makes this device suitable for the most demanding DC-DC converter applications, where high power density is to be achieved.

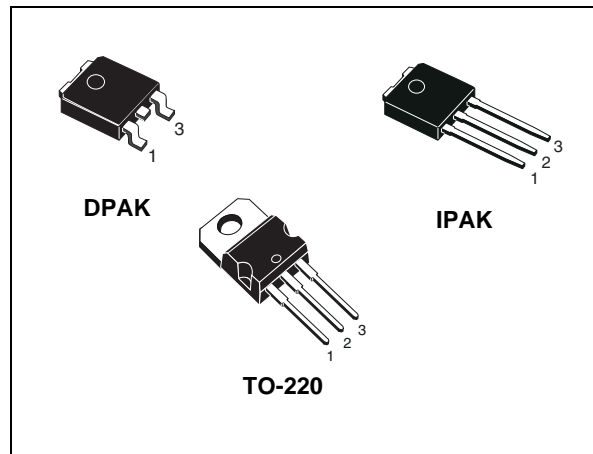


Figure 1. Internal schematic diagram

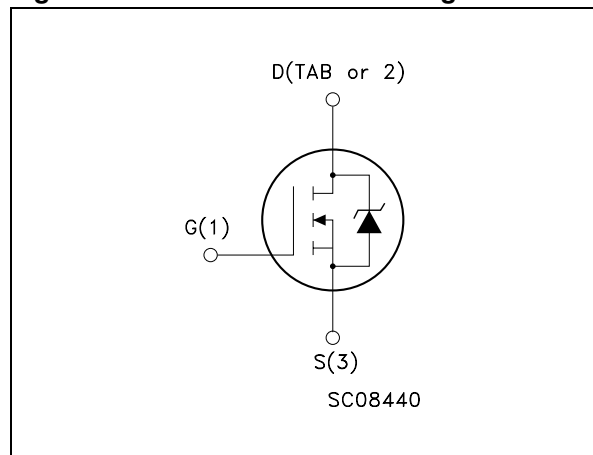


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD85N3LH5	85N3LH5	DPAK	Tape and reel
STP85N3LH5	85N3LH5	TO-220	Tube
STU85N3LH5	85N3LH5	IPAK	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuit	8
4	Package mechanical data	10
5	Packaging mechanical data	13
6	Revision history	14

www.DataSheet4U.com

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{DS}	Drain-source voltage ($V_{GS} = 0$) @ T_{JMAX}	35	V
V_{GS}	Gate-source voltage	± 22	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	55	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
	Derating factor	0.47	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	165	mJ
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature	175	$^\circ\text{C}$

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 40\text{ A}$, $V_{DD} = 25\text{ V}$

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.14	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-case max	100	$^\circ\text{C/W}$
T_j	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 20\text{ V}$ $V_{DS} = 20\text{ V}$, $T_c = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 22\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$ SMD version		0.042	0.005	Ω
		$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$		0.0046	0.0054	Ω
		$V_{GS} = 5\text{ V}$, $I_D = 40\text{ A}$ SMD version		0.0052	0.0065	Ω
		$V_{GS} = 5\text{ V}$, $I_D = 40\text{ A}$		0.0058	0.0071	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		1850		pF
C_{oss}	Output capacitance			380		pF
C_{rss}	Reverse transfer capacitance			58		pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 80\text{ A}$		14		nC
Q_{gs}	Gate-source charge	$V_{GS} = 5\text{ V}$		6.8		nC
Q_{gd}	Gate-drain charge	(see Figure 16)		4.7		nC
Q_{gs1}	Pre V_{th} gate-to-source charge	$V_{DD} = 15\text{ V}$, $I_D = 80\text{ A}$		2.3		nC
Q_{gs2}	Post V_{th} gate-to-source charge	$V_{GS} = 5\text{ V}$ (see Figure 19)		4.5		nC
R_G	Gate input resistance	$f = 1\text{ MHz}$ gate bias Bias = 0 test signal level = 20 mV open drain		1.2		Ω

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 5\text{ V}$ <i>(see Figure 15)</i>		6 14		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 5\text{ V}$ <i>(see Figure 15)</i>		23.6 10.8		ns ns

www.DataSheet4U.com

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				80 320	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$, $V_{GS} = 0$			1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$ <i>(see Figure 17)</i>		31.8 26.1 1.6		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

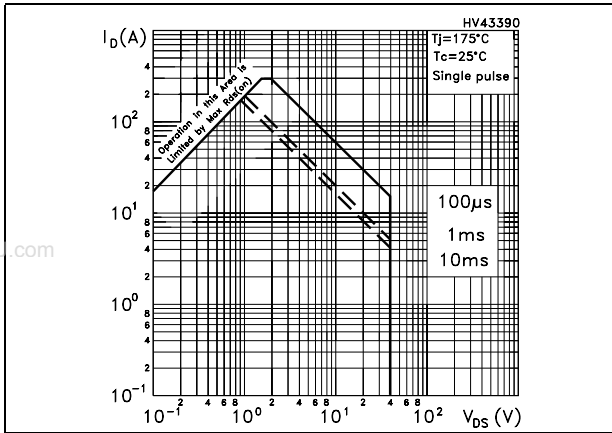


Figure 3. Thermal impedance

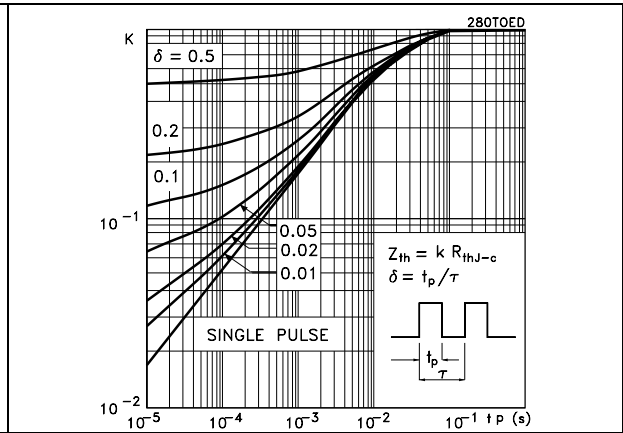


Figure 4. Output characteristics

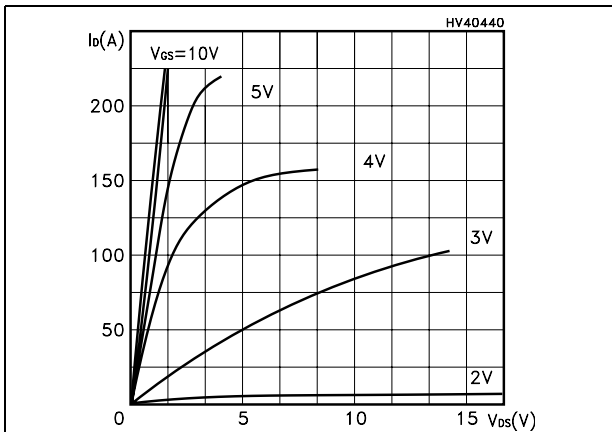


Figure 5. Transfer characteristics

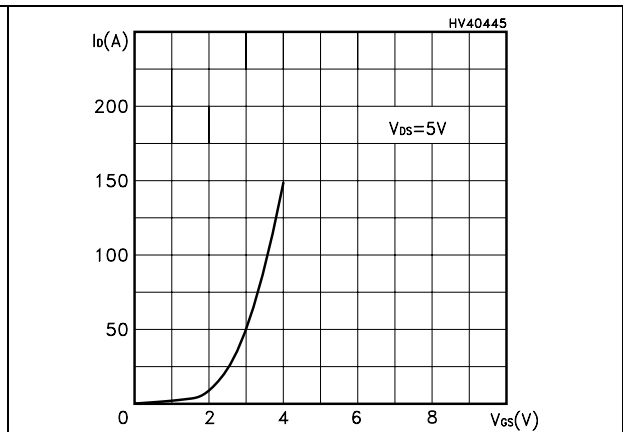


Figure 6. Normalized $B_{V_{DS}}$ vs temperature

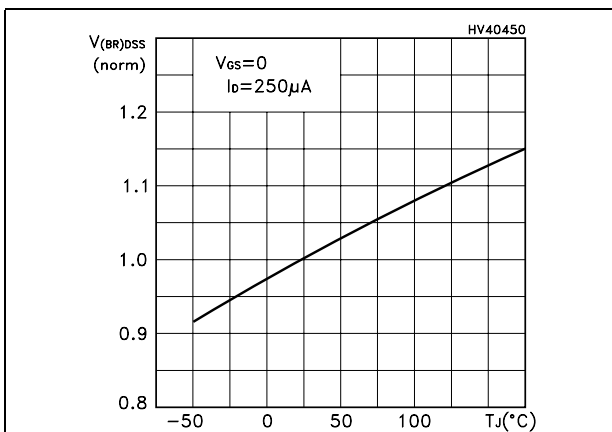


Figure 7. Static drain-source on resistance

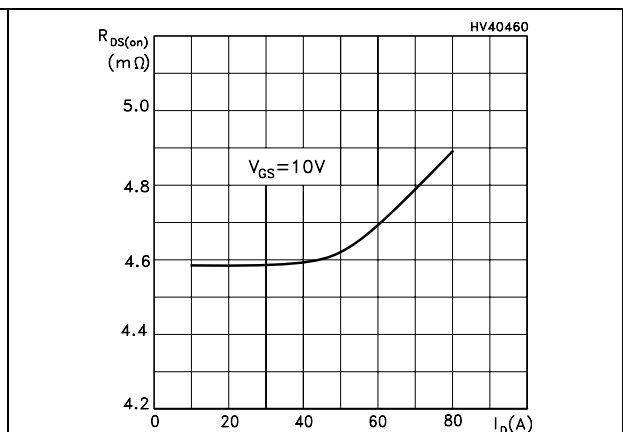


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

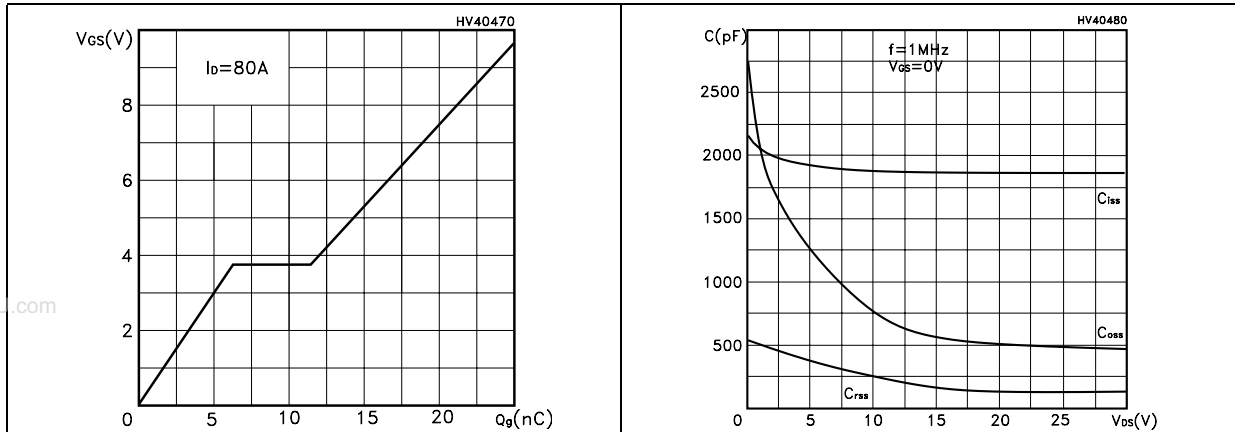


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

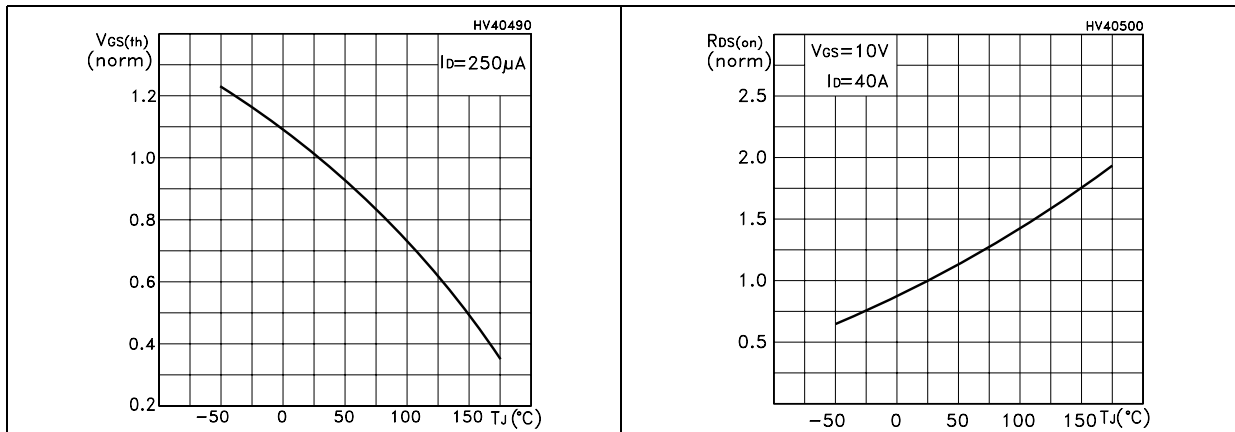
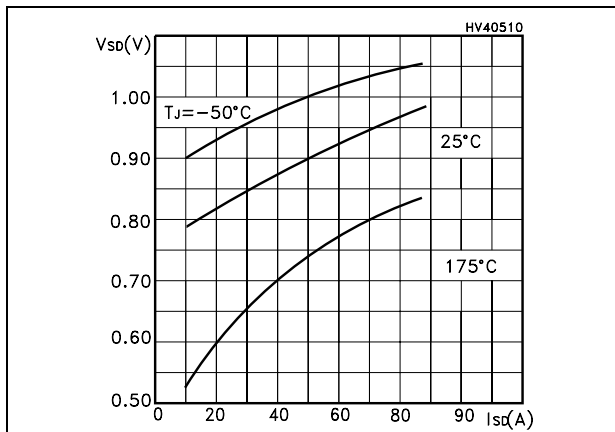


Figure 12. Source-drain diode forward characteristics



3 Test circuit

Figure 13. Unclamped inductive load test circuit

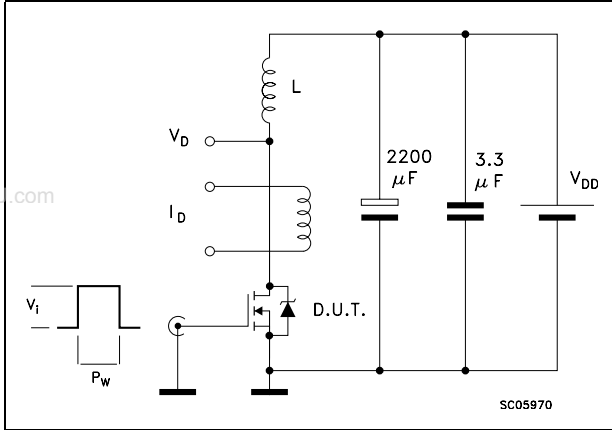


Figure 14. Unclamped inductive waveform

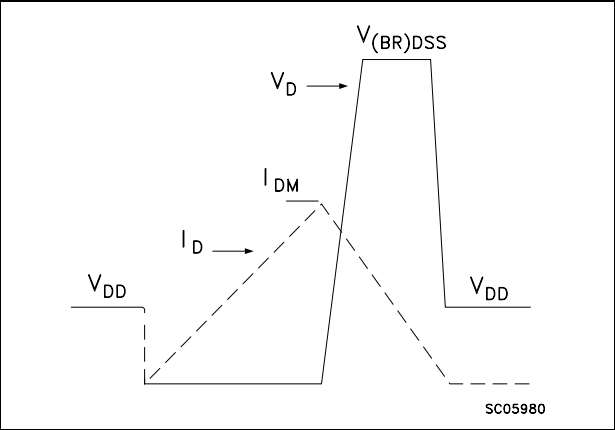


Figure 15. Switching times test circuit for resistive load

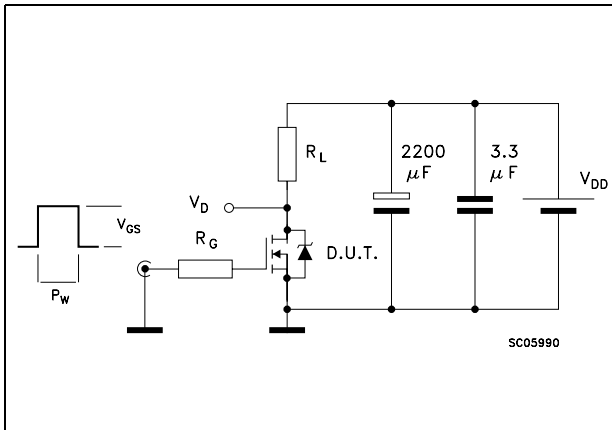


Figure 16. Gate charge test circuit

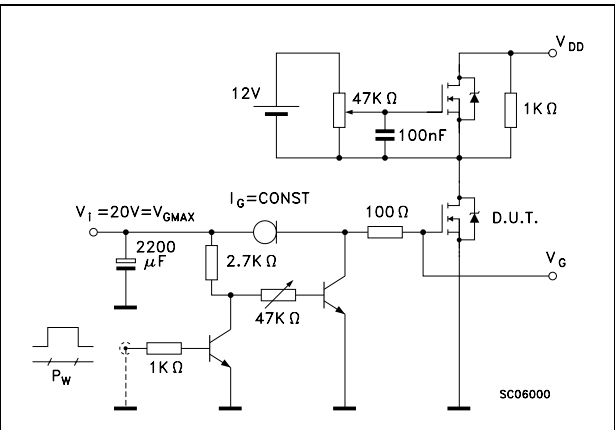


Figure 17. Test circuit for inductive load switching and diode recovery times

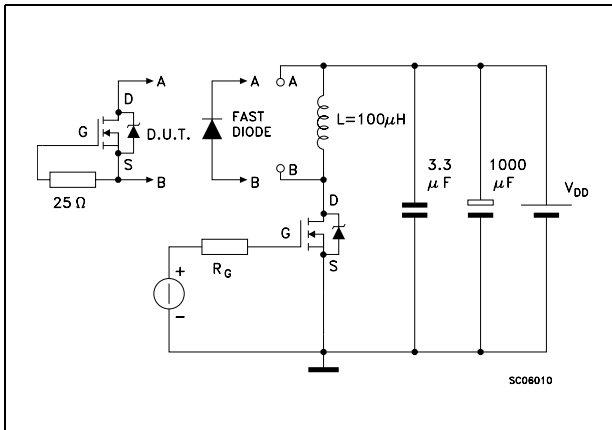


Figure 18. Switching time waveform

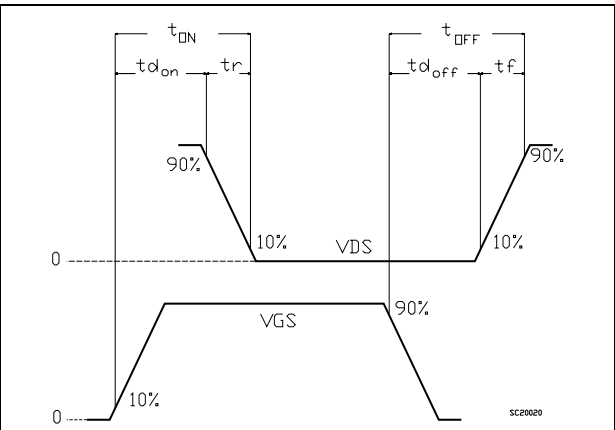
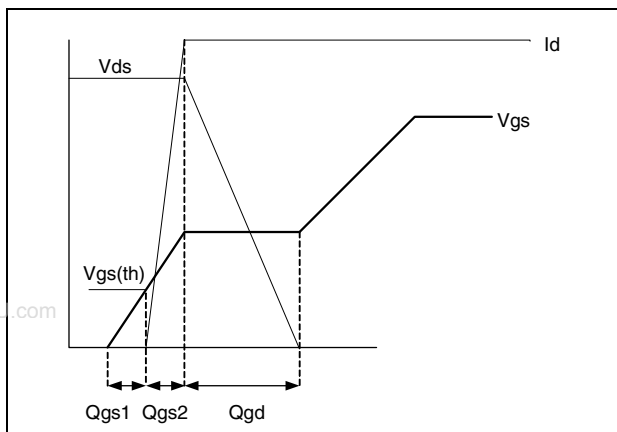


Figure 19. Gate charge waveform



www.DataSheet4U.com

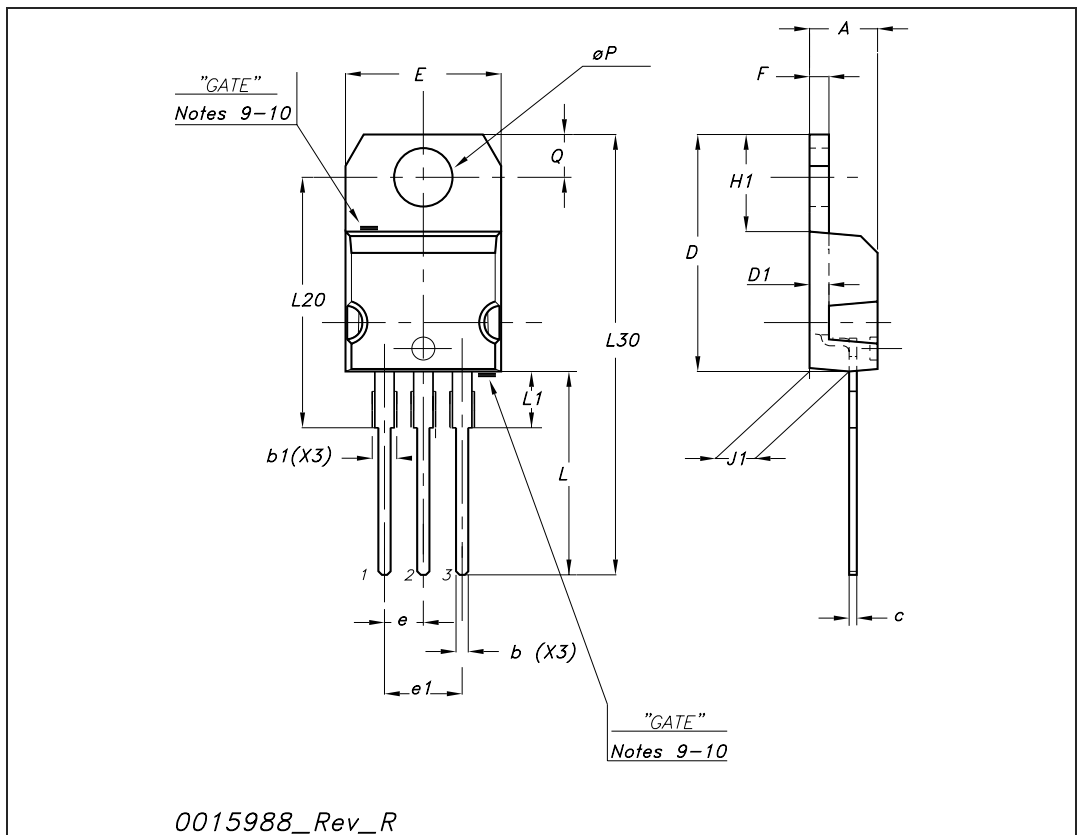
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

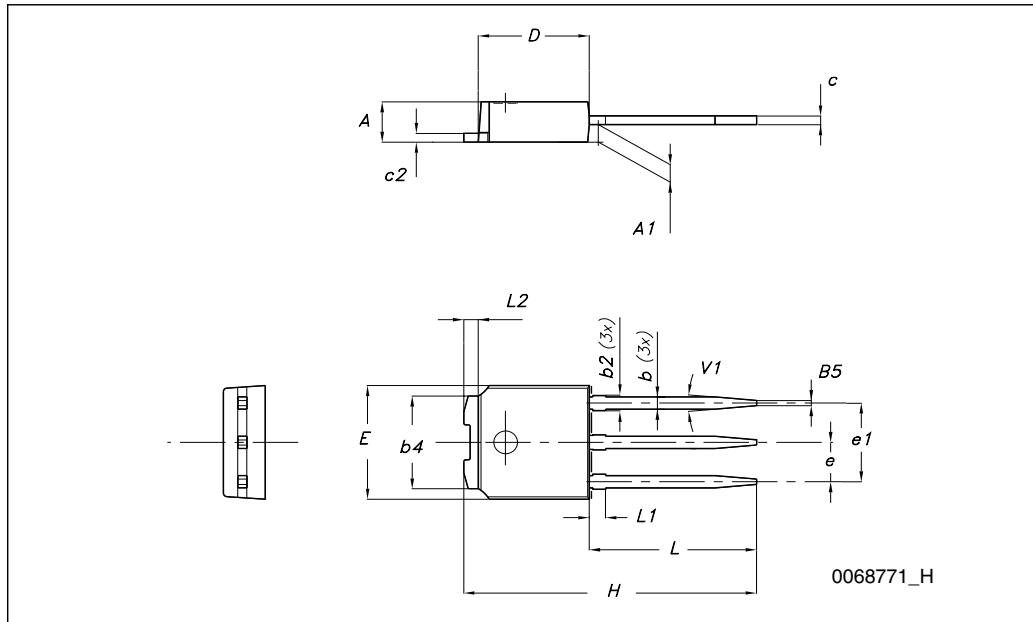
www.DataSheet4U.com



TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	

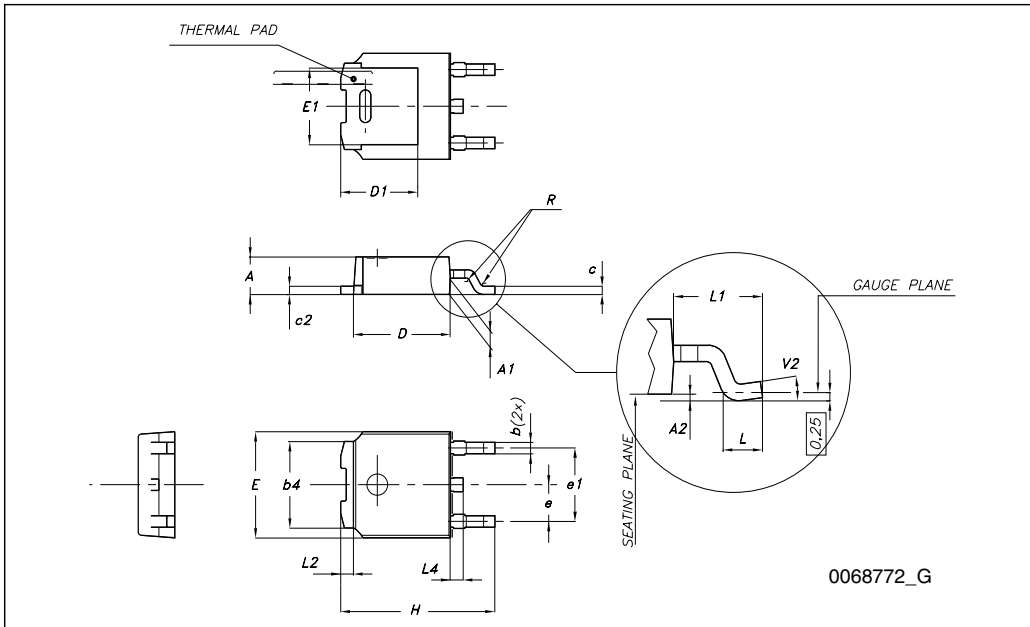
www.DataSheet4U.com



TO-252 (DPAK) mechanical data

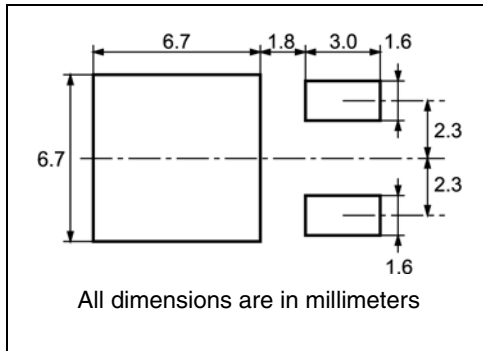
DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

www.DataSheet4U.com



5 Packaging mechanical data

DPAK FOOTPRINT



www.DataSheet4U.com

TAPE AND REEL SHIPMENT

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
19-Oct-2007	1	First release
20-Feb-2008	2	Minor text changes to improve readability
21-Jul-2008	3	<ul style="list-style-type: none">– Added new package, mechanical data: TO-220– Figure 2: Safe operating area has been corrected– Figure 7: Static drain-source on resistance updated– New value on Table 2: Absolute maximum ratings
20-Aug-2008	4	Added max value on $V_{GS(th)}$ (Table 4)
25-Sep-2008	5	V_{GS} values has been changed on Table 2 and Table 4

www.DataSheet4U.com

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2008 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com